Amendments to the Claims

1.   (Original)   A method for forming a display device, comprising:

forming a thin film transistor (TFT), a gate pad and a data pad on a substrate;

depositing sequentially an inorganic insulating material and an organic insulating material on the substrate having the TFT, the gate pad and the data pad;

selectively removing the organic insulating material using a diffracting mask to form a patterned organic insulating layer;

selectively removing the inorganic insulating material, using at least a portion of the patterned organic insulating layer as a mask to define contact holes for the TFT, the gate pad and the data pad; and

forming electrodes in the contact holes.

2.   (Original)   The method of claim 1, further comprising:

selectively removing the patterned organic insulating layer as the inorganic insulating material is removed in the step of selectively removing the inorganic insulating material.

3.   (Original)   The method of claim 1, further comprising:

removing the patterned organic insulating layer corresponding to the gate and data pads after the step of selectively removing the inorganic insulating material is performed.

4.   (Currently Amended)   The   method   of   claim   1,   further comprising:

        providing a gate insulating layer under the inorganic insulating material; and

        selectively removing portions of the gate insulating layer corresponding to the gate ~~and data pads~~ pad, using said at least a portion of the patterned organic insulating layer as a mask.

5.   (Original)   The method of claim 1, wherein, in the step of forming the electrodes, the electrodes include an electrode in contact with the gate pad and the remaining inorganic insulating material, and an electrode in contact with the data pad and the remaining inorganic insulating material.